

Amendments to the Claims:

The following listing of claims will replace all prior versions, and listings, of claims in the application:

1. (Previously Presented) A complementary transistor circuit, comprising:
 - a first transistor; and
 - a second transistor that has a conductivity type that is different from a conductivity type of the first transistor,
 - the first transistor having a first channel region formed in one single crystal grain, and
 - the second transistor having a second channel region formed in the one single crystal grain.
2. (Canceled)
3. (Previously Presented) The complementary transistor circuit according to claim 1, further comprising:
 - a first electric field relief region which is formed at both sides of the first channel region; and
 - a second electric field relief region which is formed at both sides of the second channel region,
 - the first electric field relief region and the second electric field relief region are composed of low-concentration impurity regions, and
 - the first electric field relief region and the second electric field relief region formed in the one single crystal grain.
4. (Canceled)

5. (Previously Presented) The complementary transistor circuit according to claim 1, the first transistor and the second transistor are formed in a semiconductor film in which the one single crystal grain is patterned in a U shape.
6. (Previously Presented) The complementary transistor circuit according to claim 1, the first transistor and the second transistor formed in a semiconductor film in which the one single crystal grain is patterned in a rectangular shape.
7. (Previously Presented) The complementary transistor circuit according to claim 1, the one single crystal grain is formed by carrying out a heat treatment on an amorphous or a polycrystalline semiconductor film.
8. (Previously Presented) The complementary transistor circuit according to claim 7, the one single crystal grain is formed substantially centered on a starting-point portion that is a concave portion formed on an insulating substrate.
9. (Previously Presented) The complementary transistor circuit according to claim 8, the one single crystal grain is formed by carrying out the heat treatment on the semiconductor film under a condition that the semiconductor film in the concave portion is not melted and the remaining portions are melted.
10. (Currently Amended) The complementary transistor circuit according to claim 9, the heat treatment being laser irradiation.
11. (Previously Presented) The complementary transistor circuit according to claim 7, the one single crystal grain being a silicon single crystal grain formed by carrying out the heat treatment on the amorphous or the polycrystalline silicon film.
12. (Previously Presented) An electro-optical device, comprising:
the complementary transistor circuit according to claim 1.
13. (Previously Presented) An electronic apparatus comprising:
the complementary transistor circuit according to claim 1.

14. (Currently Amended) A complementary thin film transistor circuit, comprising:

a first-conductivity-type thin film transistor and a second-conductivity-type thin film transistor formed using ~~same a~~ single crystal ~~grains~~grain, the single crystal ~~grains~~grain being formed substantially centered on ~~each of a plurality of~~ pre-positioned starting-point ~~portions~~portion disposed on an insulating surface of a substrate.

15. (Previously Presented) The complementary thin film transistor circuit according to claim 14, further comprising:

electric field relief regions which are formed at both sides of channel regions of the first-conductivity-type thin film transistor and the second-conductivity-type thin film transistor, the channel regions being sandwiched between the electric field relief regions, which are composed of low-concentration impurity regions,

the electric field relief regions and the channel regions formed in the same single crystal grain.

16. (Previously Presented) The complementary thin film transistor circuit according to claim 14, further comprising channel regions formed in a region in the single crystal grain that does not include the starting-point portion.

17. (Previously Presented) The complementary thin film transistor circuit according to claim 16, the first-conductivity-type thin film transistor and the second-conductivity-type thin film transistor formed in a semiconductor film in which the single crystal grain is patterned in a U shape.

18. (Previously Presented) The complementary thin film transistor circuit according to claim 16, the first-conductivity-type thin film transistor and the second-conductivity-type thin film transistor formed in a semiconductor film in which the single crystal grain is patterned in a rectangular shape.

19. (Previously Presented) The complementary thin film transistor circuit according to claim 14, the single crystal grain formed by carrying out a heat treatment on an amorphous or a polycrystalline semiconductor film.

20. (Previously Presented) The complementary thin film transistor circuit according to claim 19, the starting-point portion being a concave portion formed on an insulation substrate.

21. (Previously Presented) The complementary transistor circuit according to claim 1, the first transistor and the second transistor being formed on an insulating film.

22. (Previously Presented) The complementary transistor circuit according to claim 21, the first channel region and the second channel region not overlapping a concave portion formed in the insulating film.

23. (Previously Presented) A semiconductor device, comprising:
a plurality of complementary transistor circuits accordingly to claim 1.